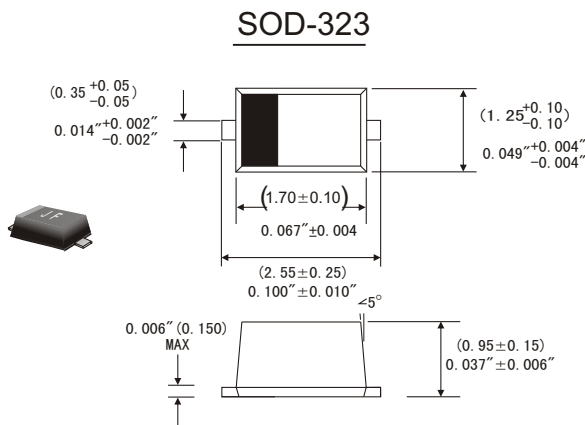


FEATURES

- Total power dissipation: max. 300 mW
- Small plastic package suitable for surface mounted design
- High reliability
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MECHANICAL DATA

- Case: SOD-323 plastic case
- Weight: Approx. 0.004 gram



Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES) (TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation	P _{tot}	300	mW
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

	Symbols	Min	Typ	Max	Units
Thermal resistance junction to ambient	R _{θJA}			0.3	K/mW
Forward voltage at I _F =10mA	V _F			0.9	V

MM3Z... SILICON PLANAR ZENER DIODES

Type	Marking Code	Zener Voltage range ¹⁾			Dynamic resistance ²⁾		Reverse leakage current		Temp Coefficient of zener voltage
		V _{ZNOM}	I _{ZT} for V _{ZT}		r _{Zj} and r _{Zjk} at I _{Zk}		I _r	at V _r	TK _{vz}
		V	mA	V	Ω	mA	μA	V	%/K
MM3Z2V0B	B0	2.0	5	1.8...2.15	100	5	120	0.5	-0.09...-0.06
MM3Z2V2B	MF	2.2	5	2.08...2.33	100	5	120	0.7	-0.09...-0.06
MM3Z2V4B	7C	2.4	5	2.3...2.65	100	5	120	1	-0.09...-0.06
MM3Z2V7B	7D	2.7	5	2.65...2.95	110	5	120	1	-0.09...-0.06
MM3Z3V0B	7E	3.0	5	2.95...3.25	120	5	50	1	-0.08...-0.05
MM3Z3V3B	7F	3.3	5	3.25...3.55	120	5	20	1	-0.08...-0.05
MM3Z3V6B	7H	3.6	5	3.6...3.845	100	5	10	1	-0.08...-0.05
MM3Z3V9B	7J	3.9	5	3.89...4.16	100	5	5	1	-0.08...-0.05
MM3Z4V3B	7K	4.3	5	4.17...4.43	100	5	5	1	-0.06...-0.03
MM3Z4V7B	7M	4.7	5	4.55...4.75	100	5	2	1	-0.05...+0.02
MM3Z5V1B	7N	5.1	5	4.98...5.2	80	5	2	1.5	-0.02...+0.02
MM3Z5V6B	7P	5.6	5	5.49...5.73	60	5	1	2.5	-0.05...+0.05
MM3Z6V2B	7R	6.2	5	6.06...6.33	60	5	1	3	0.03...0.06
MM3Z6V8B	7X	6.8	5	6.65...6.93	40	5	0.5	3.5	0.03...0.07
MM3Z7V5B	7Y	7.5	5	7.28...7.6	30	5	0.5	4	0.03...0.07
MM3Z8V2B	7Z	8.2	5	8.02...8.36	30	5	0.5	5	0.03...0.08
MM3Z9V1B	8A	9.1	5	8.85...9.23	30	5	0.5	6	0.03...0.09
MM3Z10B	8B	10	5	9.77...10.21	30	5	0.1	7	0.03...0.1
MM3Z11B	8C	11	5	10.76...11.22	30	5	0.1	8	0.03...0.11
MM3Z12B	8D	12	5	11.74...12.24	30	5	0.1	9	0.03...0.11
MM3Z13B	8E	13	5	12.91...13.49	37	5	0.1	10	0.03...0.11
MM3Z15B	8F	15	5	14.34...14.98	42	5	0.1	11	0.03...0.11
MM3Z16B	8H	16	5	15.85...16.51	50	5	0.1	12	0.03...0.11
MM3Z18B	8J	18	5	17.56...18.35	65	5	0.1	13	0.03...0.11
MM3Z20B	8K	20	5	19.52...20.39	85	5	0.1	15	0.03...0.11
MM3Z22B	8M	22	5	21.54...22.47	100	5	0.1	17	0.04...0.12
MM3Z24B	8N	24	5	23.72...24.78	120	5	0.1	19	0.04...0.12
MM3Z27B	8P	27	5	26.19...27.53	150	2	0.1	21	0.04...0.12
MM3Z30B	8R	30	5	29.19...30.69	200	2	0.1	23	0.04...0.12
MM3Z33B	8X	33	5	32.15...33.79	250	2	0.1	25	0.04...0.12
MM3Z36B	8Y	36	5	35.07...36.87	300	2	0.1	27	0.04...0.12
MM3Z39B	8Z	39	5	37...41	100	2	2	30	0.04...0.12

1) Tested with pulses tp=20ms.

2) Z_z is measured at I_z by given a very small A. C. current signal.

MM3Z... SILICON PLANAR ZENER DIODES

FIG.1-Effect of Zener Voltage on Zener Impedance

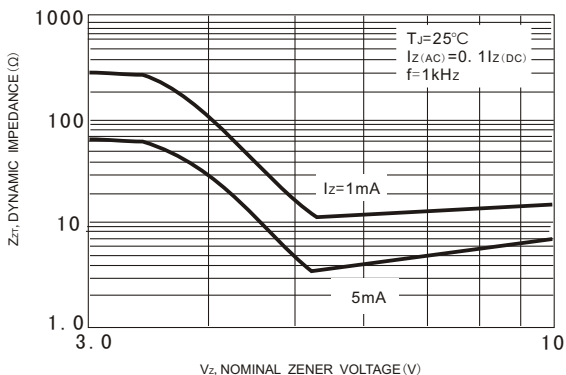


FIG.2-Typical Forward Voltage

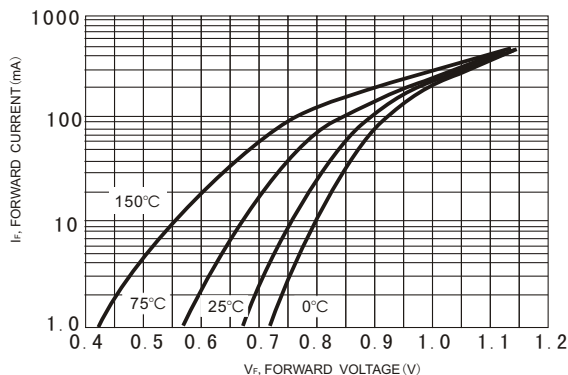


FIG.3-Typical Capacitance

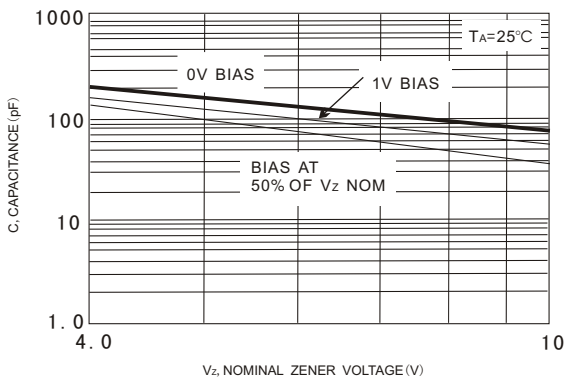


FIG.4-typical leakage current

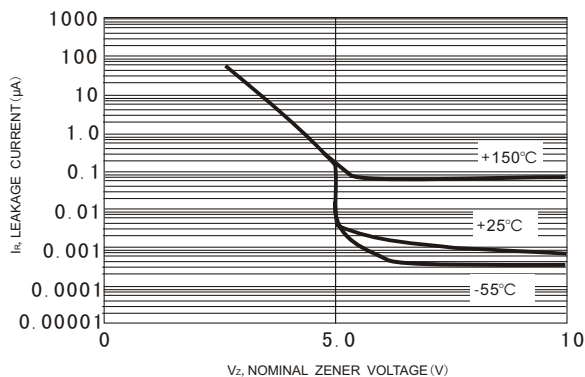


FIG.5-Zener Voltage versus Zener Current

